

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMMC.020AUSAPPLICATION NO.
09/997,396INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Hujanen et al.FILING DATE
November 28, 2001GROUP
2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
DV	1	6,143,658	11/07/00	Donnelly et al.			
DV	2	5,939,334	08/17/99	Nguyen et al.			

EXAMINER
INITIAL

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

DV

3 Ueno et al., "Cleaning of CHF3 plasma-etched SiO2/SiN/Cu via structures using a hydrogen plasma, an oxygen plasma, and hexafluoracetylacetone vapors," J. Vac. Sci. Technology B 16(6), pp. 2986-2995 (1998)

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011304

EXAMINER

Shuland

DATE CONSIDERED 08/23/04

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